

General Description

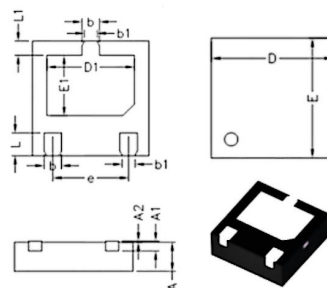
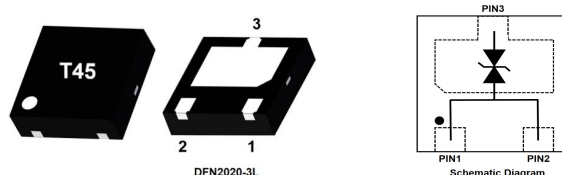
The **GS4V5H20B** is designed to protect voltage sensitive components from damage or latch-up due to surge current. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to surge current protection for board level. Because of its small size and bi-directional design, it is ideal for use in cellular phones and portable applications that require audio line protection.

Specification Features

- Small Body Outline Dimensions: nom 0.078" x 0.078" (2.0x2.0 mm)
- Low Clamping Voltage: $V_C=25V@I_{PP}=380A$
- Reverse Working (Stand-off) Voltage: 4.5 V
- Low Leakage
- Response Time is Typically < 1 ns
- IEC61000-4-2 Level 4 ESD Protection

Application

- Mobile Internet Devices (MID) and portable devices
- TVs and monitors
- PAD
- Cellular handsets and accessories
- Set-top boxes and game consoles
- Peripherals



DFN2020-3L

	Millimeters			Inches		
	Min. (mm)	Typ. (mm)	Max. (mm)	Min. (mm)	Typ. (mm)	Max. (mm)
D	1.95	2.00	2.05	0.076	0.078	0.080
E	1.95	2.00	2.05	0.076	0.078	0.080
D1	1.45	1.50	1.55	0.057	0.059	0.061
E1	1.00	1.05	1.10	0.039	0.041	0.043
L1	0.20	0.25	0.30	0.007	0.009	0.011
L	0.35	0.40	0.45	0.013	0.015	0.017
b1	0.22REF			0.025bsc		
b	0.25	0.30	0.35	0.009	0.011	0.013
e	1.30REF					
A1	0.150REF			0.005REF		
A2	0.00	0.02	0.05	0.000	-	0.001
A	0.45	0.50	0.55	0.017	0.019	0.021

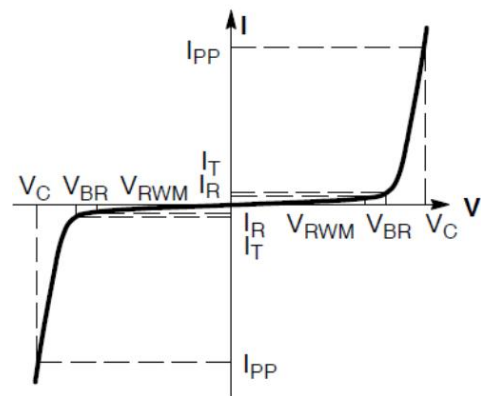
Absolute Maximum Rating

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact		±30	kV
Peak Power Per 8 x 20μs Waveform	P_{PK}	9500	W
Junction Temperature Range	T_J	55 to +150	°C
Storage Temperature Range	T_{stg}	55 to +150	
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	°C

GS4V5H20B

Characteristics($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T
P_{PK}	Peak Power Dissipation
C	Max. Capacitance @ $V_R = 0$ and freq.=1 MHz



Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				4.5	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1\text{mA}$	4.6		6	V
Reverse Leakage Current	I_R	$V_{RWM}=4.5\text{V}$			0.1	μA
Clamping Voltage	V_C	$I_{PP}=150\text{A}$ $t_p=8/20\mu\text{s}$			18	V
		$I_{PP}=380\text{A}$ $t_p=8/20\mu\text{s}$			25	
Junction Capacitance	C_J	$V_R=0\text{V}$, $f = 1\text{MHz}$		1180	1300	pF